

**REMARKS**

The 2 June 2004 official action addressed claims 1-20. Claims 1-14 were allowed and claims 16 and 19 were indicated to be allowable. By the present amendments, the features of claim 19 are incorporated into independent claim 15, placing claim 15 and its dependent claims in condition for allowance. Thus all claims are now allowable on that basis.

Claim 15 has also been amended to clarify that silicon is formed in trenches of a silicon germanium layer in contact with the silicon germanium at the trench surfaces. Claim 15 was rejected as being obvious over the combination of Liang (U.S. 6,071,783) and Chung (U.S. 5,943,575), each of which forms a semiconductor material in trenches in the source and drain regions of a MOSFET. However, in each reference the trench is lined with an insulating material before being filled, see Liang Figs. 3-5, Chung Figs. 3b-3e. Directly forming silicon in contact with the silicon germanium of trench surfaces in source and drain regions is contrary to the practices taught by both Liang and Chung, and so claim 15 is distinguished on this additional basis.

New claim 21 depends from claim 1 and recites this feature with respect to the method of claim 1.

The foregoing amendments and remarks address all bases for objection and rejection and are believed to place the case in condition for allowance. The examiner is invited to contact the undersigned to resolve any remaining issues.

Respectfully submitted,

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